

LINEAR POWER TRANSISTOR

DESCRIPTION:

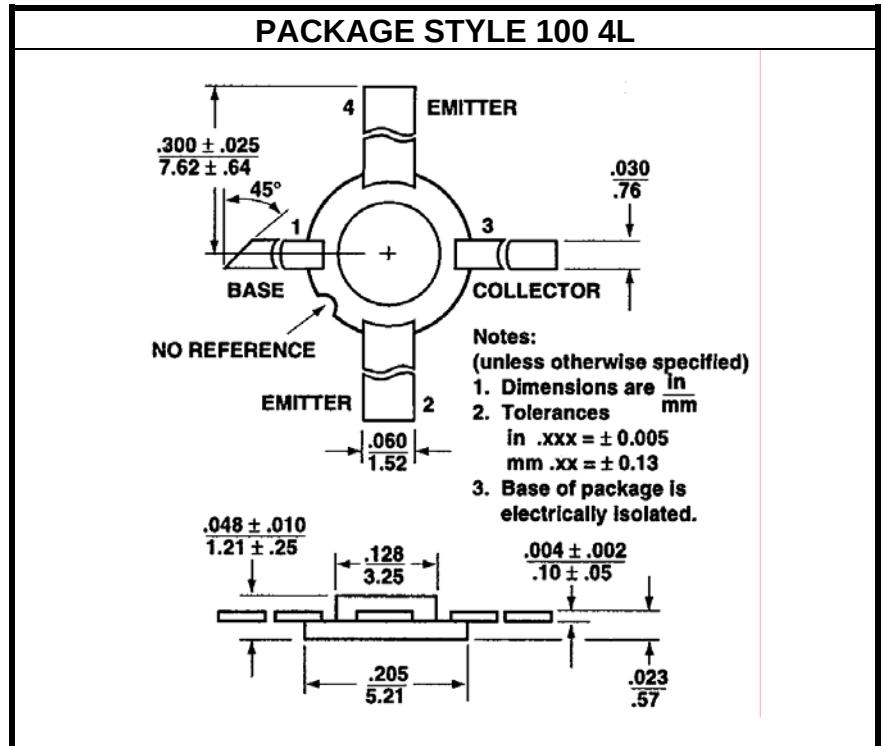
The **ASI HXTR5104** is a Common Base Device Designed for high poutput power and gain at VHF, UHF, and microwave frequency applications.

FEATURES INCLUDE:

- High Gain
- Hermetic package
- High power output

MAXIMUM RATINGS

I_C	250 mA
V_{CBO}	45 V
V_{CEO}	27 V
P_{DISS}	4.0 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+200^\circ\text{C}$
θ_{JC}	44 $^\circ\text{C/W}$



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 10\text{ mA}$	40			V
BV_{CEO}	$I_C = 50\text{ mA}$	24			V
BV_{EBO}	$I_E = 100\text{ }\mu\text{A}$	3.3			V
I_{EBO}	$V_{EB} = 2.0\text{ V}$			10	μA
I_{CES}	$V_{CE} = 32\text{ V}$			200	nA
I_{CBO}	$V_{CB} = 20\text{ V}$			100	nA
H_{FE}	$V_{CE} = 18\text{ V}$ $I_C = 110\text{ mA}$	15		85	---
C_{CB}	$V_{CB} = 10$ $f = 1.0\text{ MHz}$		0.70		pF
P_{1dB}	$V_{CE} = 18\text{ V}$ $I_C = 110\text{ mA}$ $f = 2.0\text{ GHz}$	28	29		dBm
G_{1dB}		8.0	9.0		dBm
η			35		%